

Kyung Jean Yoon

List of Publications by Year in descending order

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2329
citing authors

#	ARTICLE	IF	CITATIONS
1	A Review of Three-Dimensional Resistive Switching Crossbar Array Memories from the Integration and Materials Property Points of View. <i>Advanced Functional Materials</i> , 2014, 24, 5316-5339.	14.9	319
2	Highly Uniform, Electroforming-Free, and Self-Rectifying Resistive Memory in the Pt/Ta ₂ O ₅ /HfO ₂ /TiN Structure. <i>Advanced Functional Materials</i> , 2014, 24, 5086-5095.	14.9	197
3	Highly Improved Uniformity in the Resistive Switching Parameters of TiO ₂ Thin Films by Inserting Ru Nanodots. <i>Advanced Materials</i> , 2013, 25, 1987-1992.	21.0	170
4	32 Å— 32 Crossbar Array Resistive Memory Composed of a Stacked Schottky Diode and Unipolar Resistive Memory. <i>Advanced Functional Materials</i> , 2013, 23, 1440-1449.	14.9	152
5	Pt/Ta ₂ O ₅ /HfO ₂ /Ti Resistive Switching Memory Competing with Multilevel NAND Flash. <i>Advanced Materials</i> , 2015, 27, 3811-3816.	21.0	152
6	Nociceptive Memristor. <i>Advanced Materials</i> , 2018, 30, 1704320.	21.0	116
7	Electronic resistance switching in the Al/TiO _x /Al structure for forming-free and area-scalable memory. <i>Nanoscale</i> , 2015, 7, 11063-11074.	5.6	78
8	Memristive tri-stable resistive switching at ruptured conducting filaments of a Pt/TiO ₂ /Pt cell. <i>Nanotechnology</i> , 2012, 23, 185202.	2.6	69
9	Titanium dioxide thin films for next-generation memory devices. <i>Journal of Materials Research</i> , 2013, 28, 313-325.	2.6	67
10	Improved endurance of resistive switching TiO ₂ thin film by hourglass shaped Magn@li filaments. <i>Applied Physics Letters</i> , 2011, 98, .	3.3	65
11	What Will Come After Vertical Resistive Switching Memory?. <i>Advanced Electronic Materials</i> , 2019, 5, 1800914.	5.1	61
12	Fabrication of a Cone-Shaped Cation Source Inserted Conductive Bridge Random Access Memory and Its Improved Switching Reliability. <i>Advanced Functional Materials</i> , 2019, 29, 1806278.	14.9	51
13	Double-Layer-Stacked One Diode-One Resistive Switching Memory Crossbar Array with an Extremely High Rectification Ratio of 10 ⁹ . <i>Advanced Electronic Materials</i> , 2017, 3, 1700152.	5.1	42
14	Substrate Dependent Growth Behaviors of Plasma-Enhanced Atomic Layer Deposited Nickel Oxide Films for Resistive Switching Application. <i>Chemistry of Materials</i> , 2012, 24, 4675-4685.	6.7	36
15	A Stateful Logic Family Based on a New Logic Primitive Circuit Composed of Two Antiparallel Bipolar Memristors. <i>Advanced Intelligent Systems</i> , 2020, 2, 1900082.	6.1	36
16	Evolution of the shape of the conducting channel in complementary resistive switching transition metal oxides. <i>Nanoscale</i> , 2014, 6, 2161-2169.	5.6	35
17	Comprehensive Writing Margin Analysis and its Application to Stacked one Diode-One Memory Device for High-Density Crossbar Resistance Switching Random Access Memory. <i>Advanced Electronic Materials</i> , 2016, 2, 1600326.	5.1	34
18	Uniform Self-rectifying Resistive Switching Behavior via Preformed Conducting Paths in a Vertical-type Ta ₂ O ₅ /HfO ₂ Structure with a Sub-1/4m ² Cell Area. <i>ACS Applied Materials & Interfaces</i> , 2016, 8, 18215-18221.	8.0	34

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19	Fully Functional Logic-In-Memory Operations Based on a Reconfigurable Finite-State Machine Using a Single Memristor. <i>Advanced Electronic Materials</i> , 2018, 4, 1800189.	5.1	33
20	Schottky diode with excellent performance for large integration density of crossbar resistive memory. <i>Applied Physics Letters</i> , 2012, 100, .	3.3	32
21	In-Memory Stateful Logic Computing Using Memristors: Gate, Calculation, and Application. <i>Physica Status Solidi - Rapid Research Letters</i> , 2021, 15, 2100208.	2.4	25
22	A crossbar resistance switching memory readout scheme with sneak current cancellation based on a two-port current-mode sensing. <i>Nanotechnology</i> , 2016, 27, 485201.	2.6	24
23	Filament Shape Dependent Reset Behavior Governed by the Interplay between the Electric Field and Thermal Effects in the Pt/TiO ₂ /Cu Electrochemical Metallization Device. <i>Advanced Electronic Materials</i> , 2017, 3, 1600404.	5.1	24
24	Comparison of the Atomic Layer Deposition of Tantalum Oxide Thin Films Using Ta(N ^{it}) ₂ ₃ , Ta(N ^{it}) ₂ ₂ Cp, and H ₂ O. <i>ACS Applied Materials & Interfaces</i> , 2017, 9, 537-547.	8.0	23
25	Single-Cell Stateful Logic Using a Dual-Bit Memristor. <i>Physica Status Solidi - Rapid Research Letters</i> , 2019, 13, 1800629.	2.4	23
26	A study of the transition between the non-polar and bipolar resistance switching mechanisms in the TiN/TiO ₂ /Al memory. <i>Nanoscale</i> , 2016, 8, 16455-16466.	5.6	22
27	Ionic bipolar resistive switching modes determined by the preceding unipolar resistive switching reset behavior in Pt/TiO ₂ /Pt. <i>Nanotechnology</i> , 2013, 24, 145201.	2.6	19
28	Resistance switching behavior of atomic layer deposited SrTiO ₃ film through possible formation of Sr ₂ Ti ₆ O ₁₃ or Sr ₁ Ti ₁₁ O ₂₀ phases. <i>Scientific Reports</i> , 2016, 6, 20550.	3.3	17
29	Interface engineering for improving reliability of resistance switching in Cu/HfO ₂ /TiO ₂ /Pt structure. <i>Applied Physics Letters</i> , 2015, 107, .	3.3	16
30	Optimization of Chemical Structure of Schottky-Type Selection Diode for Crossbar Resistive Memory. <i>ACS Applied Materials & Interfaces</i> , 2012, 4, 5338-5345.	8.0	9
31	Control of conducting filaments in TiO ₂ films by a thin interfacial conducting oxide layer at the cathode. <i>Applied Physics Letters</i> , 2013, 102, 082903.	3.3	7
32	Resistive Memory: 32 × 32 Crossbar Array Resistive Memory Composed of a Stacked Schottky Diode and Unipolar Resistive Memory (Adv. Funct. Mater. 11/2013). <i>Advanced Functional Materials</i> , 2013, 23, 1350-1350.	14.9	2
33	Weight Update Generation Circuit Utilizing Phase Noise of Integrated Complementary Metal-Oxide-Semiconductor Ring Oscillator for Memristor Crossbar Array Neural Network-Based Stochastic Learning. <i>Advanced Intelligent Systems</i> , 2020, 2, 2000011.	6.1	2
34	In-Memory Hamming Error-Correcting Code in Memristor Crossbar. <i>IEEE Transactions on Electron Devices</i> , 2022, 69, 3700-3707.	3.0	2
35	Next-Generation Memory: Double-Layer-Stacked One Diode-One Resistive Switching Memory Crossbar Array with an Extremely High Rectification Ratio of 10 ⁹ (Adv. Electron. Mater. 7/2017). <i>Advanced Electronic Materials</i> , 2017, 3, .	5.1	1
36	Stateful logic circuit and material using memristors. , 2017, , .		0

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37	Cu cone inserted CBRAM device fabrication and its improved switching reliability induced by field concentration effect. , 2018, , .		0